

**HF/VHF power transistor**

**BLW50F**

**Description:**

N-P-N silicon planar epitaxial transistor primarily intended for use in class-A, AB and B operated, industrial and military transmitters in the HF and VHF band. Resistance stabilization provides protection against device damage at severe load mismatch conditions. Matched hFE groups are available on request.

**Features:**

It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

**Data:**

MODE OF OPERATION	V <sub>CE</sub> V	f MHz	P <sub>L</sub> W	G <sub>p</sub> dB	η <sub>dt</sub> %	I <sub>C</sub> A	I <sub>C(zs)</sub> mA	d <sub>3</sub> dB	T <sub>h</sub> °C
s.s.b. (class-A)	45	1,6 - 28	0 - 16 (P.E.P.)	> 19,5	-	1,2	-	< -40	70
s.s.b. (class-AB)	50	1,6 - 28	10 - 65 (P.E.P.)	typ. 18	typ. 45 <sup>(1)</sup>	1,45	50	typ. -30	25

**Drawings:**

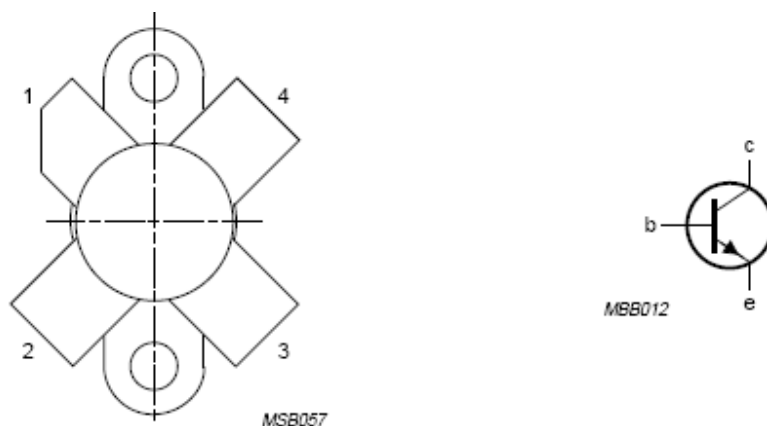


Fig.1 Simplified outline and symbol.

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter